



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

SOT-23 Plastic-Encapsulate Diodes

MMBD4148A/SE/CC/CA SWITCHING DIODES

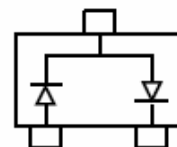
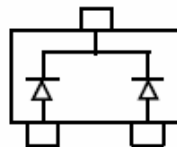
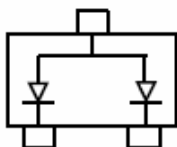
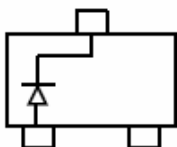
SOT-23



FEATURES

Power Dissipation

PD : 350 mW ($T_{amb}=25^{\circ}\text{C}$)



MARKING:

MMBD4148A:5H

MMBD4148CA :D6

MMBD4148CC :D5

MBD4148SE :D4

Maximum Ratings @ $T_A=25$

Parameter	Symbol	Limits	Unit
Peak Repetitive Peak reverse voltage	V_{RRM}	100	V
Working Peak Reverse Voltage	V_{RWM}		
DC Blocking Voltage	V_R		
Forward Continuous Current	I_{FM}	200	mA
Power Dissipation	P_d	350	mW
Storage temperature	T_{STG}	-55-150	$^{\circ}\text{C}$

Electrical Characteristics@ $T_A=25^{\circ}\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Reverse Breakdown Voltage	$V_{(BR)R1}$	100			V	$I_R=100\mu\text{A}$
	$V_{(BR)R2}$	75			V	$I_R=5\mu\text{A}$
Forward voltage	V_F			1	V	$I_F=10\text{mA}$
Reverse current	I_{R1}			25	nA	$V_R=25\text{V}$
	I_{R2}			5	uA	$V_R=75\text{V}$
Diode Capacitance	C_D			4	pF	$V_R=0\text{V}, f=1\text{MHz}$
Reverse Recovery Time	t_{rr}			4	nS	$I_F=10\text{mA}, V_R=6\text{V}$ $I_{rr}=0.1I_{R}, R_L=100\Omega$

Typical Characteristics

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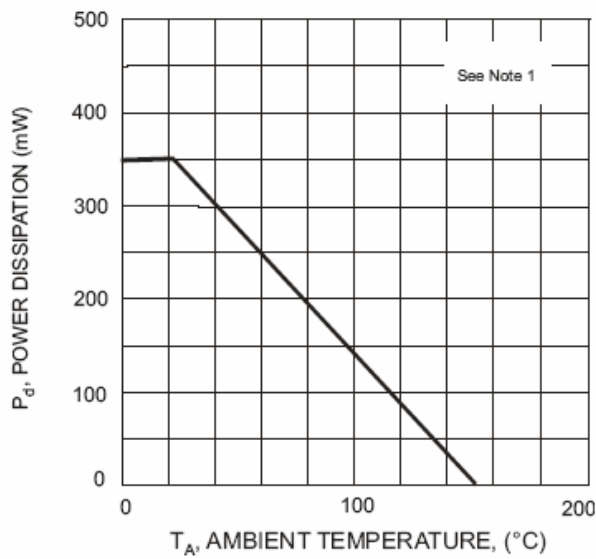


Fig. 1 Power Derating Curve

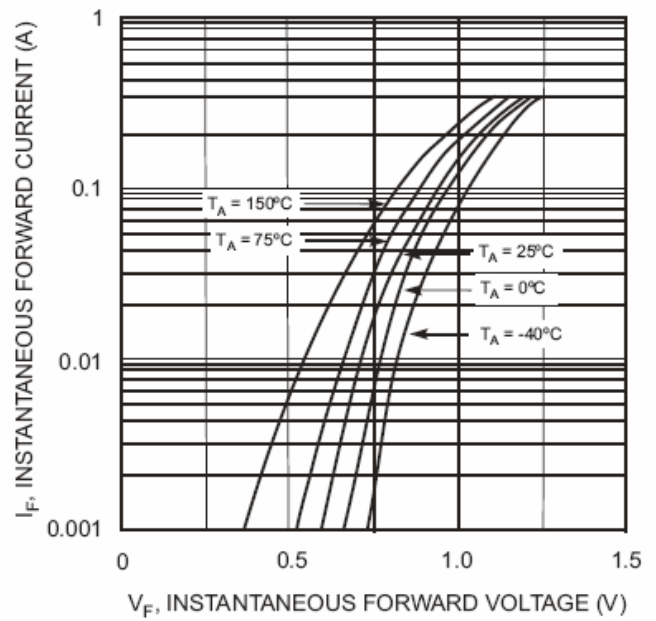


Fig. 2 Forward Characteristics

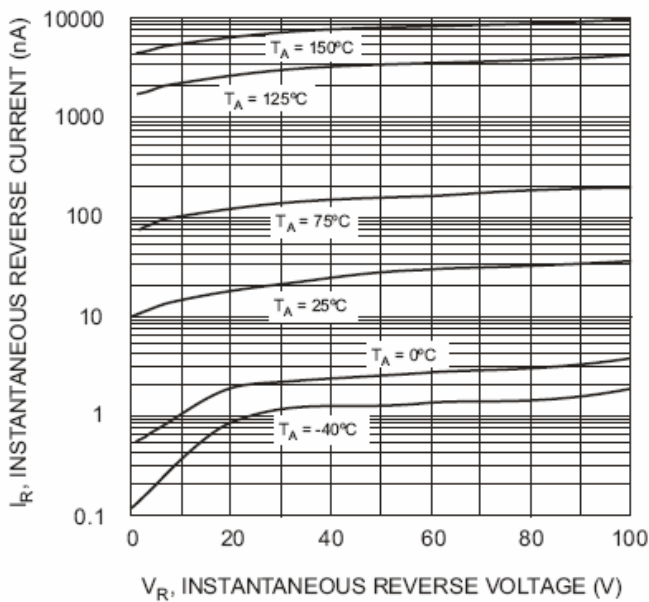


Fig. 3 Typical Reverse Characteristics

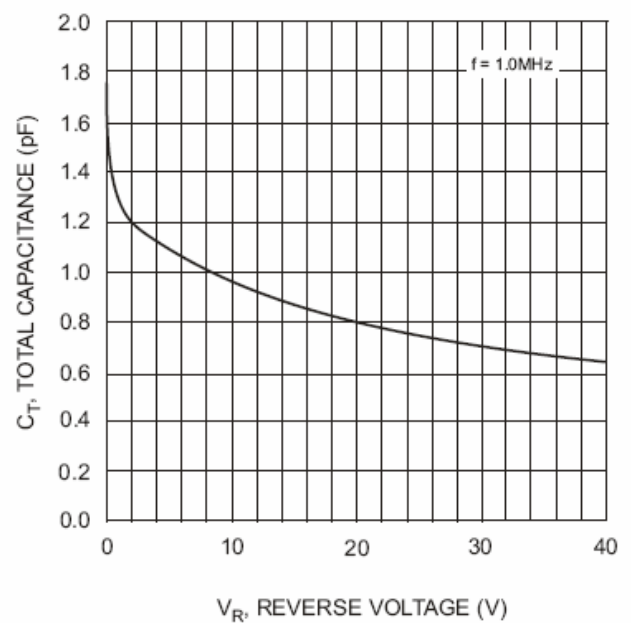


Fig. 4 Typical Capacitance vs. Reverse Voltage